

ABSTRACT

A semiconductor single crystal manufacturing apparatus which can manufacture a single crystal of high oxygen concentration to that of low oxygen concentration within a prescribed standard range of oxygen concentration, as a wafer material for semiconductor integrated circuits, with a high yield, is provided. Heat shields 20, 21 are provided in the entire annular area between respective adjacent heaters of the heaters 4a, 4b, 4c for heating the crucible 3 from the outside periphery side. By using the heat shields 20, 21 for localizing the respective heating regions for the heaters to actively control the temperature distribution for the crucible 3 and melt 8 in the crucible, a single crystal of high oxygen concentration to that of low oxygen concentration can be manufactured within a prescribed standard range of oxygen concentration with a high yield.